

Silicon PNP Power Transistors

MJE2955T

DESCRIPTION

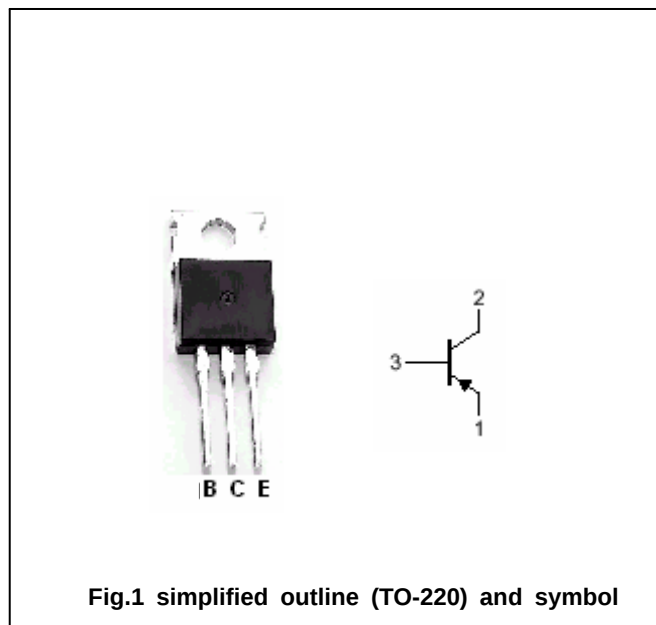
- With TO-220 package
- Complement to type MJE3055T
- DC current gain $-h_{FE} = 20-70$ @ $I_C = -4$ Adc
- Collector-emitter saturation voltage -
 $V_{CE(sat)} = -1.1$ Vdc (Max) @ $I_C = -4$ Adc

APPLICATIONS

- Designed for general-purpose switching and amplifier applications.

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings($T_a =$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-70	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-10	A
I_B	Base current		-6	A
P_C	Collector power dissipation	$T_C = 25$	75	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	1.67	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =-0.2A ; I _B =0	-60			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-4A ; I _B =-0.4A			-1.1	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-10A ; I _B =-3.3A			-8.0	V
V _{BE}	Base-emitter on voltage	I _C =-4A ; V _{CE} =-4V			-1.8	V
I _{CEO}	Collector cut-off current	V _{CE} =-30V ; I _B =0			-0.7	mA
I _{CEx}	Collector cut-off current	V _{CE} =-70V ; V _{BE(off)} =-1.5V T _C =150			-1.0 -5.0	mA
I _{CBO}	Collector cut-off current	V _{CB} =-70V ; I _E =0 T _C =150			-1.0 -10	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V ; I _C =0			-5.0	mA
h _{FE-1}	DC current gain	I _C =-4A ; V _{CE} =-4V	20		100	
h _{FE-2}	DC current gain	I _C =-10A ; V _{CE} =-4V	5.0			
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-10V	2.0			MHz

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PACKAGE OUTLINE

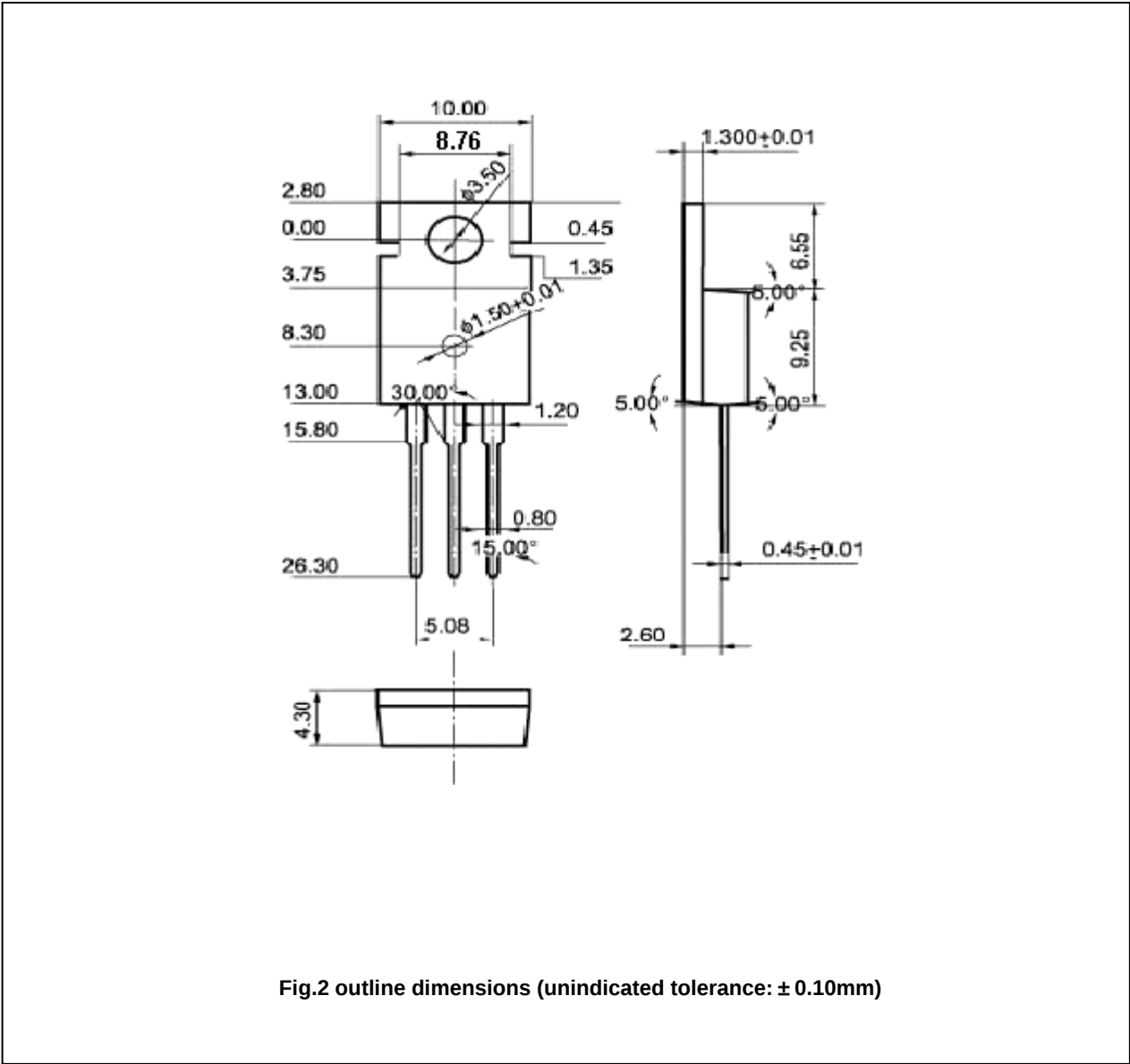


Fig.2 outline dimensions (unindicated tolerance: ± 0.10mm)